

## Photoluminescence spectroscopy of thin sheets of Gallium Selenide

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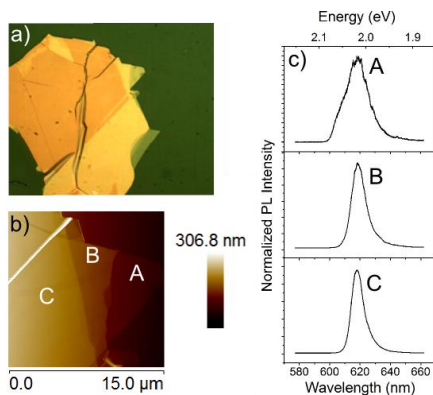
Interest in atomically thin two-dimensional (2D) layered compounds, including metal chalcogenides, has increased in recent years due to unique physical properties of a few monolayer (ML) structures [1], and also growing effort in fabrication of novel heterostructures composed of layered materials. So far, main focus in studies of light-emitting layered materials was on MoS<sub>2</sub>, which however shows dramatic decrease in photoluminescence (PL) for sheets with thicknesses above single ML [2]. Here we present low-temperature micro-PL ( $\mu$ -PL) studies of thin sheets of mechanically exfoliated thin layers of GaSe capped with a thin SiN layer. We show that GaSe exhibit significantly brighter PL than MoS<sub>2</sub> around 2.05 eV for layers up to 160 nm thick.  $\mu$ -PL enables observation of unusual sharp lines (with linewidths 3-10 meV) possibly originating from quantum-confined states in very thin dislocated layers embedded within quasi-bulk GaSe sheets. Our results indicate significant enhancement of exciton binding energies in such dislocated layers potentially enabling wider range of applications of GaSe in light emitting opto-electronic devices.

[1] Novoselov, K.S., et al., Nature 490, 192–200 (2012)

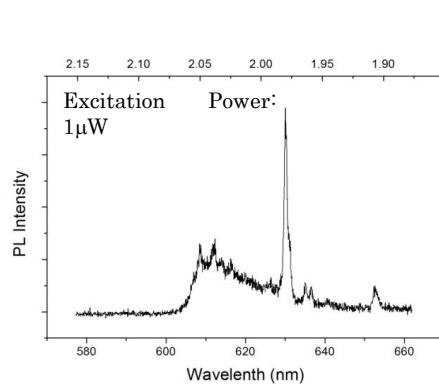
[2] Qing Hua Wang et al., Nature Nanotechnology 7, 699-712 (2012).

[3] Mooser E. et al., Il Nuovo Cimento, Vol. 18 B, N. 1, 164 (1973).

[4] PyngAn Hu et al., American Chemical Soc. Vol. 6, 7, 5988 (2012).



**Fig.1.** a) Optical image of a mechanically exfoliated GaSe thin flake. b) AFM image of a region of the flake shown in (a). Three different thicknesses are observed. c) Photoluminescence (PL) spectra measured for three different places of the flake (A, B and C).



**Fig.2.** PL spectra of a GaSe thin flake measured with excitation power of 1  $\mu$ W. Narrow lines appear with low excitation power at lower energies than the main PL line.